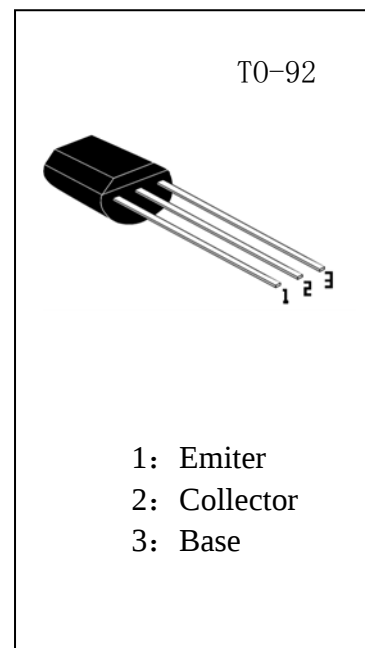


大电流低压晶体管

- 电流输出最大达 3A
- 低饱和电压
- 与 2SB772 对管

极限参数(Absolute Maximum Ratings) Ta=25°C

Characteristic	Symbol	Rating	Unit
CollectorBase Voltage	Vcbo	40	V
CollectorEmitter Voltage	Vceo	30	V
EmitterBase Voltage	Vebo	5	V
Collector Current (DC)	Ic	3	A
Collector Current (PLUSE)	Ic	7	A
Base current	Ib	0.6	A
Collector Dissipation	Pc	750	m W
Junction Temperature	Tj	150	°C
Storage Temperature	Tstg	-55~150	°C



电性能(Electrical Characteristic) Ta=25°C

Symbol	Characteristic	Test Condition	Min	Typ	Max	Unit
BVcbo	CollectorBase Breakdown Voltage	Ic=100uA Ie=0	40			V
BVceo	CollectorEmitter Breakdown Voltage	Ic=1mA Ib=0	30			V
BVebo	EmitterBase Breakdown Voltage	Ie=100uA Ic=0	5			V
Icbo	Collector Cutoff Current	Vcb=30V, Ie=0			1	uA
Iebo	Emitter Cutoff Current	Veb=3V, Ic=0			1	uA
Iceo	Collector Cutoff Current	Vce=20V, Ib=0			10	uA
Vce(sat)	CollectorEmitter Saturation Voltage	Ic=2A, Ib=0.2A		0.3	0.5	V
Vbe(sat)	BaseEmitter Saturation Voltage	Ic=2A, Ib=0.2A		1	2	V
Hfe1	DC Current Gain	Vce=2V, Ic=20mA	30	200		
Hfe2	DC Current Gain	Vce=2V, Ic=1A	100	150	400	
Cob	Output Capacitance	Vcb=10V, Ie=0, f=1MHz		45		PF
fT	Current GainBandwidth product	Vce=5V, Ic=0.1A		80		MHz

Class	Q	P	E
Hfe2	100-160	160-320	320-400